

OVLFx3C7

Features:

- High brightness with well-defined spatial radiation patterns
- UV-resistant epoxy lens
- 30° Beam Angle



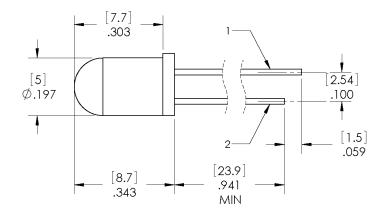
Description:

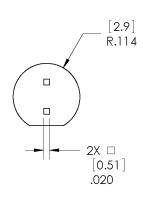
Each device in the OVLFx3C7 series is a high-intensity LED mounted in a clear plastic T-1¾ package. The LED provides a well-defined and even emission pattern. The UV-resistant epoxy lens makes this device an optimal solution for outdoor applications.

Applications:

- Traffic and pedestrian signals
- Signage and architectural lighting
- Backlighting
- Automotive

Part Numbe	er Material	Emitted Color	Intensity Typ. mc	d Lens Color
OVLFB3C7	InGaN	Blue	5,200	Clear
OVLFG3C7	InGaN	Green	16,000	Clear
OVLFR3C7	AllnGaP	Red	7,400	Clear
OVLFY3C7	AllnGaP	Yellow	7,400	Clear







1 ANODE

2 CATHODE

DIMENSIONS ARE IN INCHES AND [MILLIMETERS].

ATTENTION

OBSERVE PRECAUTIONS
ELECTROSTATIC
SENSITIVE DEVICES

Leadframe material is iron alloy with tin-plated leads

DO NOT LOOK DIRECTLY
AT LED WITH
UNSHIELDED EYES OR
DAMAGE TO RETINA MAY





Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage Temperature Range		-40 ~ +100 °C
Operating Temperature Range		-40 ~ +100 °C
Reverse Voltage		5 V
Continuous Forward Current	Blue, Green	25 mA
Continuous Forward Current	Red, Yellow	50 mA
Peak Forward Current (10% Duty Cycle, 1 kHz)	Blue, Green	100 mA
Peak Forward Current (10% Duty Cycle, 1 kHz)	Red, Yellow	100 mA
Power Dissipation	Blue, Green	100 mW
Power Dissipation	Red, Yellow	120 mW
Current Linearity vs Ambient Temperature	Blue, Green	-0.29 mA/° C
Current Linearity vs Ambient Temperature	Red, Yellow	-0.72 mA/° C
Electrostatic Discharge Classification (JEDEC-JESD22-A114F)		Class 1C
LED Junction Temperature		125° C
Lead Soldering Temperature (4 mm from the base of the epoxy bulb)		260° C / 5 seconds

Electrical Characteristics

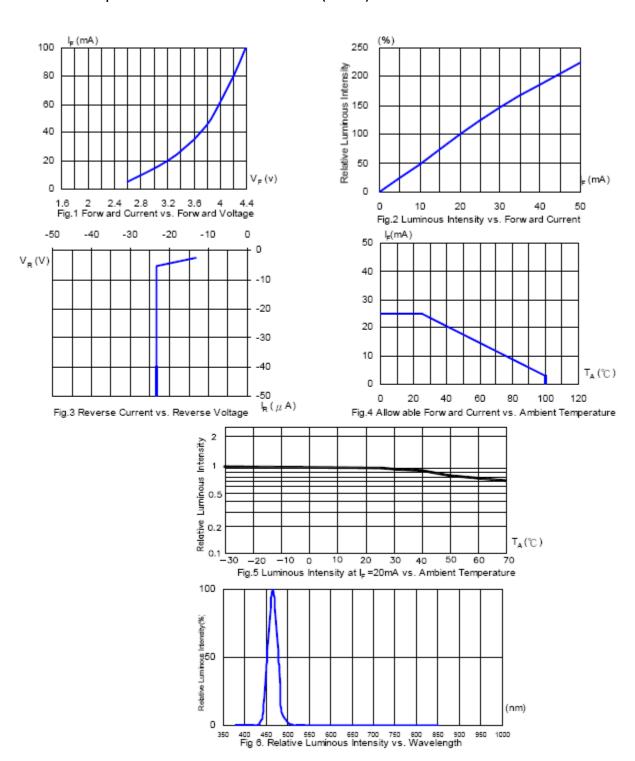
SYMBOL	PARAMETER	COLOR	MIN	ТҮР	MAX	UNITS	CONDITIONS	
I _V	Luminous Intensity	Blue	3,115	5,200		mcd		
		Green	8,550	16,000			I _F = 20 mA	
		Red	4,360	7,400			I _F = 20 IIIA	
		Yellow	4,360	7,400				
	Forward Voltage	Blue	2.6	3.4	4.0	V	I _F = 20 mA	
V _F		Green						
		Red	1.8	2.0	2.4			
		Yellow	1.6					
I _R	Reverse Current	Blue			10	μА	V _R = 5 V	
		Green						
		Red						
		Yellow						
	Dominant Wavelength	Blue	460	470	475	nm	I _F = 20 mA	
,		Green	519	525	531			
$\lambda_{ extsf{D}}$		Red	620	623	630		I _F = 20 IIIA	
		Yellow	585	589	595			
Δλ	Spectra Half Width	Blue		25		nm	I _F = 20 mA	
		Green						
		Red						
		Yellow						
20½H-H	50% Power Angle	•		30		deg	I _F = 20 mA	

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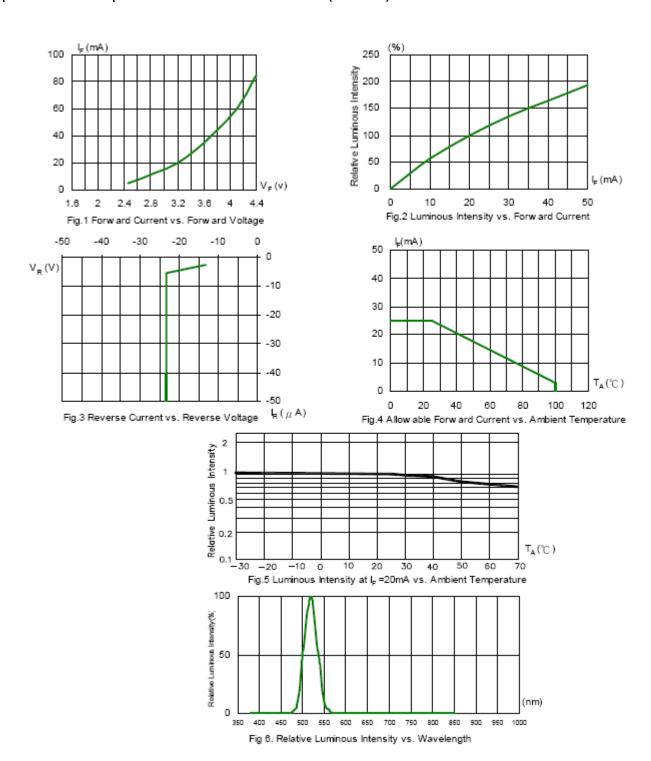
Typical Electro-Optical Characteristics Curves (BLUE)





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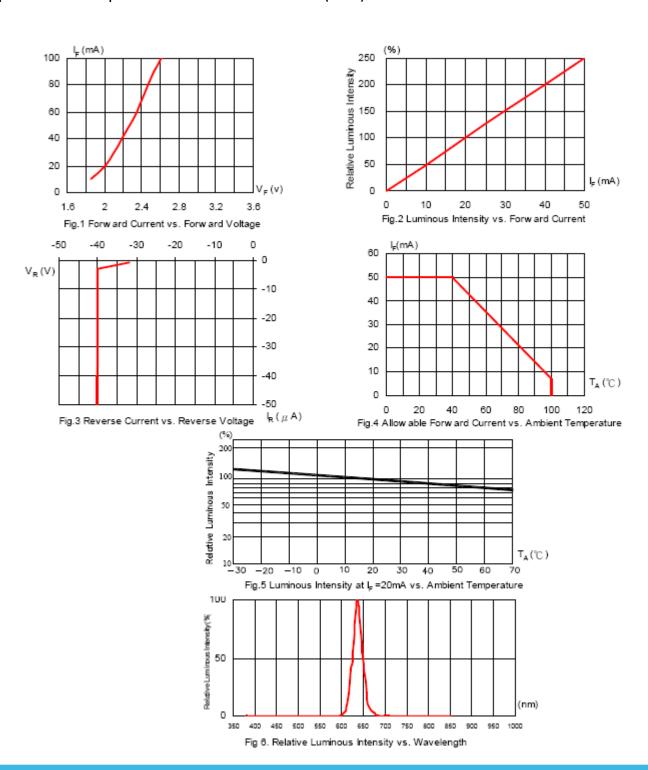
Typical Electro-Optical Characteristics Curves (GREEN)





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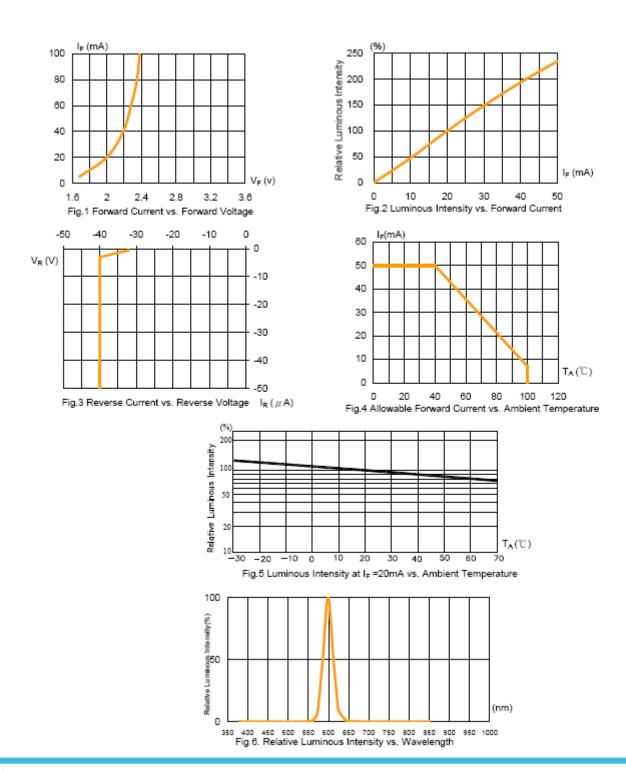
Typical Electro-Optical Characteristics Curves (RED)





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Typical Electro-Optical Characteristics Curves (YELLOW)

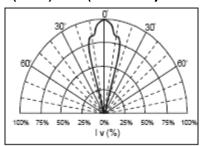




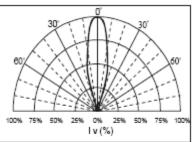


Beam Pattern

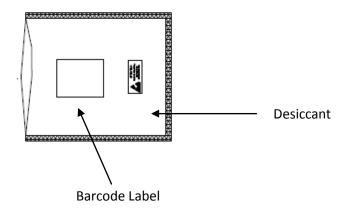
(RED) and (YELLOW)



(BLUE) and (GREEN)



Packaging: 500 pcs per bulk bag with desiccant





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Reliability Test

Classi- fication	Test Item	Standard Test Method	Test Conditions	Duration	Unit	Acc / Rej Criteria	Result
Life Test	Operation Life Test (OLT)	MIL-STD-750D Method 1026.3	$T_A=25^{\circ}C$, $I_F=30mA$ *	1000 Hrs	100	0 / 1	Pass
	High Temperature Storage (HTS)	MIL-STD-750D Method 1032.1	T _A =100°C	1000 Hrs	100	0 / 1	Pass
Environment Test Test Test	Low Temperature Storage (LTS)	MIL-STD-750D Method 1032.1	T _A =-40°C	1000 Hrs	100	0 / 1	Pass
	Temp. & Humidity with Bias (THB)	MIL-STD-750D Method 103B	T _A =85°C , Rh=85% I _F =20mA **	500 Hrs	100	0 / 1	Pass
	Thermal Shock Test (TST)	MIL-STD-750D Method 1056.1	0°C ~ 100°C 2min 2min	100 cycles	100	0 / 1	Pass
	Temperature Cycling Test (TCT)	MIL-STD-750D Method 1051.5	-40°C ~ 25°C ~ 100°C ~ 25°C 30min 5min 30min 5min	100 cycles	100	0 / 1	Pass
Mechanical Test	Solderability	MIL-STD-750D Method 2026.4	235±5℃ , 5 sec	1 time	20	0 / 1	Pass
	Resistance to Soldering Heat	MIL-STD-750D Method 2031.1	260±5°C → 10 sec	1 time	20	0 / 1	Pass
	Lead Integrity	MIL-STD-750D Method 2036.3	Load 2.5N (0.25kgf) 0°~90°~0°, bend	3 times	20	0 / 1	Pass

Remark : (*) I_F =30mA for AlInGaP chip ; I_F =20mA for InGaN chip (**) I_F =20mA for AlInGaP chip ; I_F =10mA for InGaN chip

2. Failure Criteria (T_A =25°C):

Test Item	Symbol	Test Conditions	Criteria for Judgment			
		rest Conditions	Min.	Max.		
Luminous Intensity	$I_{ m V}$	I _F =20 mA	LSL×0.7 **			
Voltage (Forward)	V_{F}	I _F =20 mA		USL×1.1 *		

(*) USL: Upper Standard Level , (**) LSL: Lower Standard Level